SDLS193 - MARCH 1974 - REVISED MARCH 1988

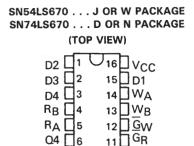
- Separate Read/Write Addressing Permits Simultaneous Reading and Writing
- Fast Access Times . . . Typically 20 ns
- Organized as 4 Words of 4 Bits
- Expandable to 512 Words of n-Bits
- For Use as:

Scratch-Pad Memory Buffer Storage between Processors Bit Storage in Fast Multiplication Designs

- 3-State Outputs
- SN54LS170 and SN74LS170 Are Similar But **Have Open-Collector Outputs**

description

The SN54LS670 and SN74LS670 MSI 16-bit TTL register files incorporate the equivalent of 98 gates. The register file is organized as 4 words of 4 bits each and separate on-chip decoding is provided for addressing the four word locations to either write-in or retrieve data. This permits simultaneous writing into one location and reading from another word location.

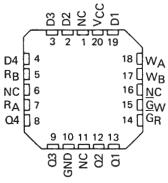


SN54LS670 . . . FK PACKAGE (TOP VIEW)

03

 \Box_7 GND ∏8 10 \ Q1

02 9 🗌



NC - No internal connection.

Four data inputs are available which are used to supply the 4-bit word to be stored. Location of the word is determined by the write-address inputs A and B in conjunction with a write-enable signal. Data applied at the inputs should be in its true form. That is, if a high-level signal is desired from the output, a high-level is applied at the data input for that particular bit location. The latch inputs are arranged so that new data will be accepted only if both internal address gate inputs are high. When this condition exists, data at the D input is transferred to the latch output. When the write-enable input, Gw, is high, the data inputs are inhibited and their levels can cause no change in the information stored in the internal latches. When the read-enable input, GR, is high, the data outputs are inhibited and go into the high-impedance state.

The individual address lines permit direct acquisition of data stored in any four of the latches. Four individual decoding gates are used to complete the address for reading a word. When the read address is made in conjunction with the read-enable signal, the word appears at the four outputs.

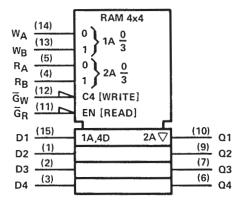
This arrangement—data-entry addressing separate from data-read addressing and individual sense line—eliminates recovery times, permits simultaneous reading and writing, and is limited in speed only by the write time (27 nanoseconds typical) and the read time (24 nanoseconds typical). The register file has a nondestructive readout in that data is not lost when addressed.

All inputs except read enable and write enable are buffered to lower the drive requirements to one Series 54LS/74LS standard load, and input-clamping diodes minimize switching transients to simplify system design. High-speed, double-ended AND-OR-INVERT gates are employed for the read-address function and have high-sink-current, three-state outputs. Up to 128 of these outputs may be bus connected for increasing the capacity up to 512 words. Any number of these registers may be paralleled to provide n-bit word length.

The SN54LS670 is characterized for operation over the full military temperature range of -55° C to 125° C; the SN74LS670 is characterized for operation from 0° C to 70° C.



logic symbol†



[†]This symbol is in accordance with ANSI/IEEE Std. 91-1984 and IEC Publication 617-12. Pin numbers shown are for D, J, N, and W packages.

WRITE FUNCTION TABLE (SEE NOTES A, B, AND C)

| WR | ITE INP | JTS | | wo | RD | |
|----|---------|-----|----------------|----------------|----------------|------------|
| WB | WA | Ğω | 0 | 1 | 2 | 3 |
| L | L | L | Q = D | α ₀ | α ₀ | σ0 |
| L | Н | L | σ ₀ | Q = D | Q_0 | Q_0 |
| Н | L | L | α ₀ | σ_0 | Q = D | Q_0 |
| Н | н | L | 00 | a_0 | Q_0 | Q = D |
| × | X | н | α ₀ | σ_0 | σ_0 | σ_0 |

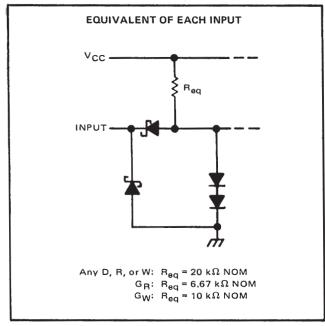
READ FUNCTION TABLE (SEE NOTES A AND D)

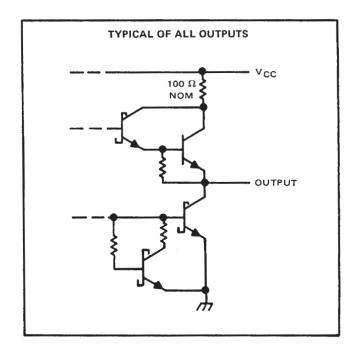
| RE | AD INPL | JTS | OUTPUTS | | | | | | | |
|----|----------------------------------|-----|---------|------|------|------|--|--|--|--|
| RB | R _B R _A GR | | Q1 | Q2 | Q3 | Q4 | | | | |
| L. | L | L | W0B1 | W0B2 | W0B3 | W0B4 | | | | |
| L | н | L | W1B1 | W1B2 | W1B3 | W1B4 | | | | |
| н | L | L | W2B1 | W2B2 | W2B3 | W2B4 | | | | |
| н | Н | L | W3B1 | W3B2 | W3B3 | W3B4 | | | | |
| × | × | н | z | Z | Z | Z | | | | |

NOTES: A. H = high level, L = low level, X = irrelevant, Z = high impedance (off)

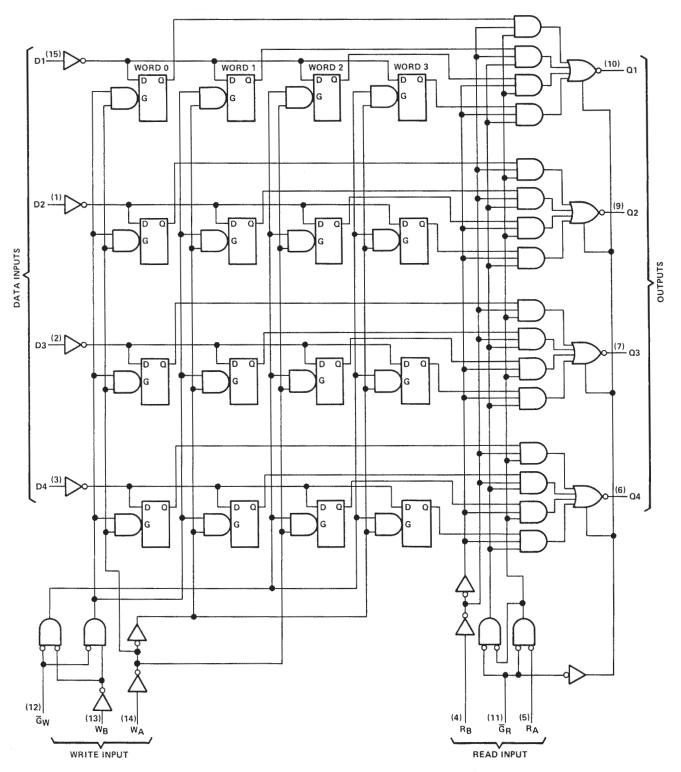
- B. (Q = D) = The four selected internal flip-flop outputs will assume the states applied to the four external data inputs.
- C. Q_0 = the level of Q before the indicated input conditions were established.
- D. W0B1 = The first bit of word 0, etc.

schematics of inputs and outputs





logic diagram (positive logic)



Pin numbers shown are for D, J, N, and W packages.



SN54LS670, SN74LS670 4-BY-4 REGISTER FILES WITH 3-STATE OUTPUTS

SDLS193 - MARCH 1974 - REVISED MARCH 1988

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

| Supply voltage, V _{CC} (see Note 1) | | | | | | | | | | | | | 7 V |
|--|-------------|------|--|--|--|--|--|--|--|------------|-----|------|---------|
| Input voltage | | | | | | | | | | | | | 7 V |
| Off-state output voltage | | | | | | | | | | | | | 5.5 V |
| Operating free-air temperature range | : SN54LS670 | | | | | | | | | — Ę | 55° | C to | 125°C |
| | SN74LS670 | | | | | | | | | | 0 | °C 1 | :o 70°C |
| Storage temperature range | | | | | | | | | | — 6 | 35° | C to | 150°C |

recommended operating conditions

| | | SI | V54LS6 | 70 | SI | 174LS6 | 70 | |
|--|--|-----|--------|-----|------|--------|-------|------|
| | | MIN | NOM | MAX | MIN | MOM | MAX | UNIT |
| Supply voltage, VCC | | 4.5 | 5 | 5.5 | 4.75 | 5 | 5.25 | V |
| High-level output current, IOH | | | | -1 | | | -2.6 | mA |
| Low-level output current, IOL | | | | 4 | | | 8 | mA |
| Width of write-enable or read-enable pulse, $t_{\rm W}$ | | 25 | | | 25 | | | ns |
| Setup times, high- or low-level data | Data input with respect to write enable, t _{su(D)} | 10 | | | 10 | | | ns |
| (see Figure 2) | Write select with respect to write enable, t _{su} (W) | 15 | | | 15 | | | ns |
| Hold times, high- or low-level data | Data input with respect to write enable, th(D) | 15 | | | 15 | | | ns |
| (see Note 2 and Figure 2) | Write select with respect to write enable, th(W) | 5 | | | 5 | | 1.11. | ns |
| Latch time for new data, t _{latch} (see Note 3) | | 25 | | | 25 | | | ns |
| Operating free-air temperature range, TA | | -55 | | 125 | 0 | | 70 | °C |

NOTES: 1. Voltage values are with respect to network ground terminal.

- 2. Write-select setup time will protect the data written into the previous address. If protection of data in the previous address is not required, $t_{su(W)}$ can be ignored as any address selection sustained for the final 30 ns of the write-enable pulse and during $t_{h(W)}$ will result in data being written into that location. Depending on the duration of the input conditions, one or a number of previous addresses may have been written into.
- 3. Latch time is the time allowed for the internal output of the latch to assume the state of new data. See Figure 2. This is important only when attempting to read from a location immediately after that location has received new data.



electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

| | DADAMETED | Tr | OT COMPLETION | ıot | SI | V54LS6 | 70 | SI | | | |
|------|---|---------------------------------------|-------------------------|----------------------------|-----|--------|------|-----|------|------|------|
| | PARAMETER | 16: | ST CONDITION | 15' | MIN | TYP‡ | MAX | MIN | TYP‡ | MAX | UNIT |
| VIH | High-level input voltage | | | | 2 | | | 2 | | | · V |
| VIL | Low-level input voltage | | | | | | 0.7 | | | 0.8 | V |
| VIK | input clamp voltage | V _{CC} = MIN, | I _I = -18 mA | | | | -1.5 | | | -1.5 | V |
| Vou | High-level output voltage | V _{CC} = MIN, | V _{IH} = 2 V, | I _{OH} = -1 mA | 2.4 | 3.4 | | | | | V |
| ٧ОН | riigii-level output voitage | V _{IL} = V _{IL} max | | $I_{OH} = -2.6 \text{ mA}$ | | | | 2.4 | 3.1 | | \ \ |
| Voi | Low-level output voltage | V _{CC} = MIN, | V _{IH} = 2 V, | I _{OL} = 4 mA | | 0.25 | 0.4 | | 0.25 | 0.4 | V |
| VOL | Low-level output voltage | VIL = VIL max | | IOL = 8 mA | | | | | 0.35 | 0.5 | V |
| lozн | Off-state output current, high-level voltage applied | V _{CC} = MAX, | V _{IH} = 2 V, | V _O = 2.7 V | | | 20 | | | 20 | μА |
| IOZL | Off-state output current, low-level voltage applied | V _{CC} = MAX, | V _{IH} = 2 V, | V _O = 0.4 V | | | -20 | | | -20 | μА |
| | Input current at | V _{CC} = MAX, | Any D, R, or I | W | | | 0.1 | | | 0.1 | |
| 4 | maximum input voltage | | \overline{G}_{W} | | | | 0.2 | | | 0.2 | mA |
| | maximum input voltage | V ₁ = 7 V | GR | | | | 0.3 | | | 0.3 | 1 |
| | | V _{CC} = MAX, | Any D, R, or | W | | | 20 | | | 20 | |
| ΉΗ | High-level input current | | Ğ₩ | | | | 40 | | | 40 | μΑ |
| | | V _I = 2.7 V | GR | | | | 60 | | | 60 | |
| | | V _{CC} = MAX, | Any D, R, or | W | | | -0.4 | | | -0.4 | |
| 11L | Low-level input current | V _I = 0.4 V | G _W | | | | -0.8 | | | -0.8 | mA |
| | | | GR | | | | -1.2 | | | -1.2 | |
| los | Short-circuit output current§ | | | | -30 | | -130 | -30 | | -130 | mA |
| Icc | Supply current | V _{CC} = MAX, | See Note 4 | | | 30 | 50 | | 30 | 50 | mA |

 $^{^\}dagger$ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.

switching characteristics, $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$

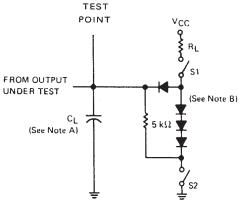
| PARAMETER | FROM (INPUT) | TO (OUTPUT) | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|-----------------|----------------|-------------------------------------|-----|-----|-----|-------|
| tPLH_ | Read select | Any Q | $C_L = 15 pF$, $R_L = 2 k\Omega$, | | 23 | 40 | |
| tPHL the tensor of the tensor | nead select | Ally C | See Figures 1 and 2 | | 25 | 45 | ns |
| ^t PLH | Write enable | Any Q | | | 26 | 45 | ns |
| ^t PHL | Witte chable | Ally Q | $C_L = 15 pF$, $R_L = 2 k\Omega$, | | 28 | 50 | 1 115 |
| t _{PLH} | Data | Any Q | See Figures 1 and 3 | | 25 | 45 | ns |
| tPHL | Data | Ally Q | | | 23 | 40 | 1115 |
| ^t PZH | | | $C_L = 15 pF$, $R_L = 2 k\Omega$, | | 15 | 35 | ns |
| tpZL | Read enable | Any Q | See Figures 1 and 4 | | 22 | 40 | 1 115 |
| t _{PHZ} | Tread chapte | Ally Q | $C_L = 5 pF$, $R_L = 2 k\Omega$, | | 30 | 50 | - 00 |
| ^t PLZ | | | See Figures 1 and 4 | | 16 | 35 | ns |

 $^{^{\}ddagger}$ All typical values are at V_{CC} = 5 V, T_{A} = 25°C.

[§]Not more than one output should be shorted at a time, and duration of the short-circuit should not exceed one second.

NOTE 4: Maximum I_{CC} is guaranteed for the following worst-case conditions: 4.5 V is applied to all data inputs and both enable inputs, all address inputs are grounded and all outputs are open.

PARAMETER MEASUREMENT INFORMATION

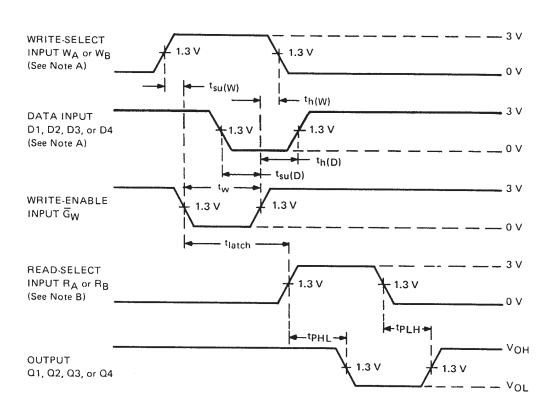


NOTES: A. $C_{\underline{L}}$ includes probe and jig capacitance.

B. All diodes are 1N3064 or equivalent.

LOAD CIRCUIT

FIGURE 1



VOLTAGE WAVEFORMS (S1 AND S2 ARE CLOSED)

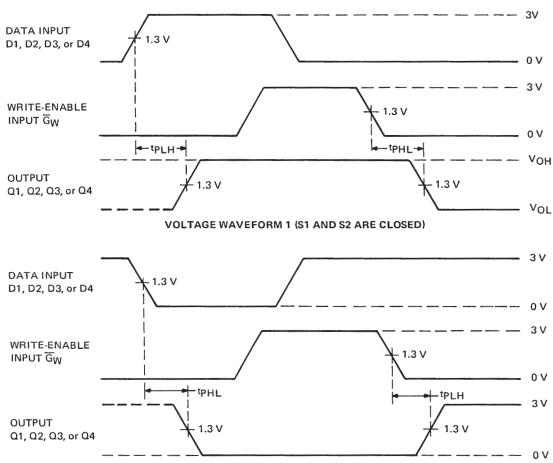
NOTES: A. High-level input pulses at the select and data inputs are illustrated; however, times associated with low-level pulses are measured from the same reference points.

- B. When measuring delay times from a read-select input, the read-enable input is low.
- C. Input waveforms are supplied by generators having the following characteristics: PRR \leq 2 MHz, $Z_{out} \approx$ 50 Ω , duty cycle \leq 50%, $t_r \leq$ 15 ns, $t_r \leq$ 6 ns.

FIGURE 2



PARAMETER MEASUREMENT INFORMATION

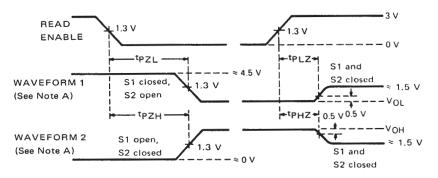


VOLTAGE WAVEFORM 2 (S1 AND S2 ARE CLOSED)

NOTES: A. Each select address is tested. Prior to the start of each of the above tests both write and read address inputs are stabilized with

 $W_A = R_A$ and $W_B = R_B$. During the test G_R is low. B. Input waveforms are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_{out} \approx$ 50 Ω , duty cycle \leq 50%, $t_r \leq$ 15 ns, $t_r \leq$ 6 ns.

FIGURE 3



VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES, THREE-STATE OUTPUTS

NOTES: A. Waveforms 1 is for an output with internal conditions such that the output is low except when disabled by the read-enable input.

Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the read-enable input.

- B. When measuring delay times from the read-enable input, both read-select inputs have been established at steady states.
- C. Input waveforms are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_{out} \approx$ 50 Ω , duty cycle \leq 50%, $t_r \leq$ 15 ns, $t_r \leq$ 6 ns.



www.ti.com

8-Jun-2023

PACKAGING INFORMATION

| Orderable Device | Status (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan | Lead finish/ Ball material | MSL Peak Temp | Op Temp (°C) | Device Marking (4/5) | Samples |
|------------------|------------|--------------|--------------------|------|----------------|---------------------|-------------------------------|--------------------|--------------|--------------------------|---------|
| 7704201EA | ACTIVE | CDIP | J | 16 | 1 | Non-RoHS & Green | SNPB | N / A for Pkg Type | -55 to 125 | 7704201EA SNJ54LS670J | Samples |
| 7704201FA | ACTIVE | CFP | W | 16 | 1 | Non-RoHS & Green | SNPB | N / A for Pkg Type | -55 to 125 | 7704201FA SNJ54LS670W | Samples |
| 7704201FA | ACTIVE | CFP | W | 16 | 1 | Non-RoHS & Green | SNPB | N / A for Pkg Type | -55 to 125 | 7704201FA SNJ54LS670W | Samples |
| SN54LS670J | ACTIVE | CDIP | J | 16 | 1 | Non-RoHS & Green | SNPB | N / A for Pkg Type | -55 to 125 | SN54LS670J | Samples |
| SN54LS670J | ACTIVE | CDIP | J | 16 | 1 | Non-RoHS & Green | SNPB | N / A for Pkg Type | -55 to 125 | SN54LS670J | Samples |
| SN74LS670D | ACTIVE | SOIC | D | 16 | 40 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | 0 to 70 | LS670 | Samples |
| SN74LS670D | ACTIVE | SOIC | D | 16 | 40 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | 0 to 70 | LS670 | Samples |
| SN74LS670N | ACTIVE | PDIP | N | 16 | 25 | RoHS & Green | NIPDAU | N / A for Pkg Type | 0 to 70 | SN74LS670N | Samples |
| SN74LS670N | ACTIVE | PDIP | N | 16 | 25 | RoHS & Green | NIPDAU | N / A for Pkg Type | 0 to 70 | SN74LS670N | Samples |
| SN74LS670NSR | ACTIVE | SO | NS | 16 | 2000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | 0 to 70 | 74LS670 | Samples |
| SN74LS670NSR | ACTIVE | SO | NS | 16 | 2000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | 0 to 70 | 74LS670 | Samples |
| SNJ54LS670FK | ACTIVE | LCCC | FK | 20 | 1 | Non-RoHS & Green | SNPB | N / A for Pkg Type | -55 to 125 | SNJ54LS 670FK | Samples |
| SNJ54LS670FK | ACTIVE | LCCC | FK | 20 | 1 | Non-RoHS & Green | SNPB | N / A for Pkg Type | -55 to 125 | SNJ54LS 670FK | Samples |
| SNJ54LS670J | ACTIVE | CDIP | J | 16 | 1 | Non-RoHS & Green | SNPB | N / A for Pkg Type | -55 to 125 | 7704201EA SNJ54LS670J | Samples |
| SNJ54LS670J | ACTIVE | CDIP | J | 16 | 1 | Non-RoHS & Green | SNPB | N / A for Pkg Type | -55 to 125 | 7704201EA SNJ54LS670J | Samples |
| SNJ54LS670W | ACTIVE | CFP | W | 16 | 1 | Non-RoHS & Green | SNPB | N / A for Pkg Type | -55 to 125 | 7704201FA SNJ54LS670W | Samples |
| SNJ54LS670W | ACTIVE | CFP | W | 16 | 1 | Non-RoHS & Green | SNPB | N / A for Pkg Type | -55 to 125 | 7704201FA SNJ54LS670W | Samples |

⁽¹⁾ The marketing status values are defined as follows:

PACKAGE OPTION ADDENDUM

www.ti.com 8-Jun-2023

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN54LS670, SN74LS670:

Catalog: SN74LS670

Military: SN54LS670

NOTE: Qualified Version Definitions:

Catalog - TI's standard catalog product

PACKAGE OPTION ADDENDUM

www.ti.com 8-Jun-2023

• Military - QML certified for Military and Defense Applications

PACKAGE MATERIALS INFORMATION

www.ti.com 9-Aug-2022

TAPE AND REEL INFORMATION





| A0 | Dimension designed to accommodate the component width |
|----|---|
| В0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

| Device | Package Type | Package Drawing | | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|--------------|-----------------|--------------------|----|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| SN74LS670NSR | SO | NS | 16 | 2000 | 330.0 | 16.4 | 8.2 | 10.5 | 2.5 | 12.0 | 16.0 | Q1 |

PACKAGE MATERIALS INFORMATION

www.ti.com 9-Aug-2022



*All dimensions are nominal

| | Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|---|--------------|--------------|-----------------|------|------|-------------|------------|-------------|
| I | SN74LS670NSR | SO | NS | 16 | 2000 | 356.0 | 356.0 | 35.0 |

PACKAGE MATERIALS INFORMATION

www.ti.com 9-Aug-2022

TUBE



*All dimensions are nominal

| Device | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | T (µm) | B (mm) |
|--------------|--------------|--------------|------|-----|--------|--------|--------|--------|
| 7704201FA | W | CFP | 16 | 1 | 506.98 | 26.16 | 6220 | NA |
| SN74LS670D | D | SOIC | 16 | 40 | 507 | 8 | 3940 | 4.32 |
| SN74LS670N | N | PDIP | 16 | 25 | 506 | 13.97 | 11230 | 4.32 |
| SN74LS670N | N | PDIP | 16 | 25 | 506 | 13.97 | 11230 | 4.32 |
| SNJ54LS670FK | FK | LCCC | 20 | 1 | 506.98 | 12.06 | 2030 | NA |
| SNJ54LS670W | W | CFP | 16 | 1 | 506.98 | 26.16 | 6220 | NA |



SOP



- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing
- per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.



SOF



NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOF



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



D (R-PDS0-G16)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



W (R-GDFP-F16)

CERAMIC DUAL FLATPACK



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only.
- E. Falls within MIL STD 1835 GDFP2-F16



8.89 x 8.89, 1.27 mm pitch

LEADLESS CERAMIC CHIP CARRIER

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



14 LEADS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2023, Texas Instruments Incorporated